# TOSHIBA

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

# **RN4906**

R1: 4.7kΩ

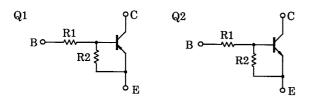
R2: 47kΩ

(Q1, Q2 Common)

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- Includeing two devices in US6 (ultra super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

#### **Equivalent Circuit and Bias Resister Values**

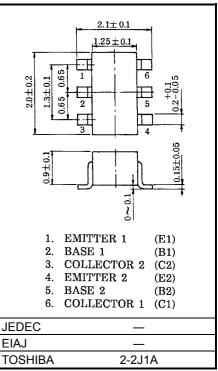


#### Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	Ι <sub>C</sub>	-100	mA

#### Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	Ι <sub>C</sub>	100	mA



Weight: 6.8mg

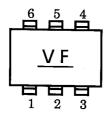
Unit: mm

#### Q1, Q2 Common Maximum Ratings (Ta = 25°C)

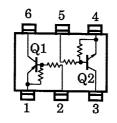
Characteristic	Symbol	Rating	Unit
Collector power dissipation	P <sub>C</sub> *	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

\* Total rating

#### Marking



## Equivalent Circuit (Top View)



## Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	_	$V_{CB} = -50V, I_E = 0$	_	_	-100	nA
	I <sub>CEO</sub>	_	$V_{CE} = -50V, I_B = 0$	_	_	-500	
Emitter cut-off current	I <sub>EBO</sub>	_	$V_{EB} = -5V, I_C = 0$	-0.074	—	-0.138	mA
DC current gain	h <sub>FE</sub>	_	V <sub>CE</sub> = −5V, I <sub>C</sub> = −10mA	80	_	_	-
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	_	I <sub>C</sub> = −5mA, I <sub>B</sub> = −0.25mA	_	-0.1	-0.3	V
Input voltage (ON)	V <sub>I (ON)</sub>	_	$V_{CE} = -0.2V, I_{C} = -5mA$	-0.7	_	-1.3	V
Input voltage (OFF)	VI (OFF)	_	$V_{CE} = -5V, I_C = -0.1mA$	-0.5	_	-0.8	V
Transition frequency	f <sub>T</sub>	_	V <sub>CE</sub> = −10V, I <sub>C</sub> = −5mA	_	200	_	MHz
Collector output capacitance	C <sub>ob</sub>	_	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0	_	3	6	pF

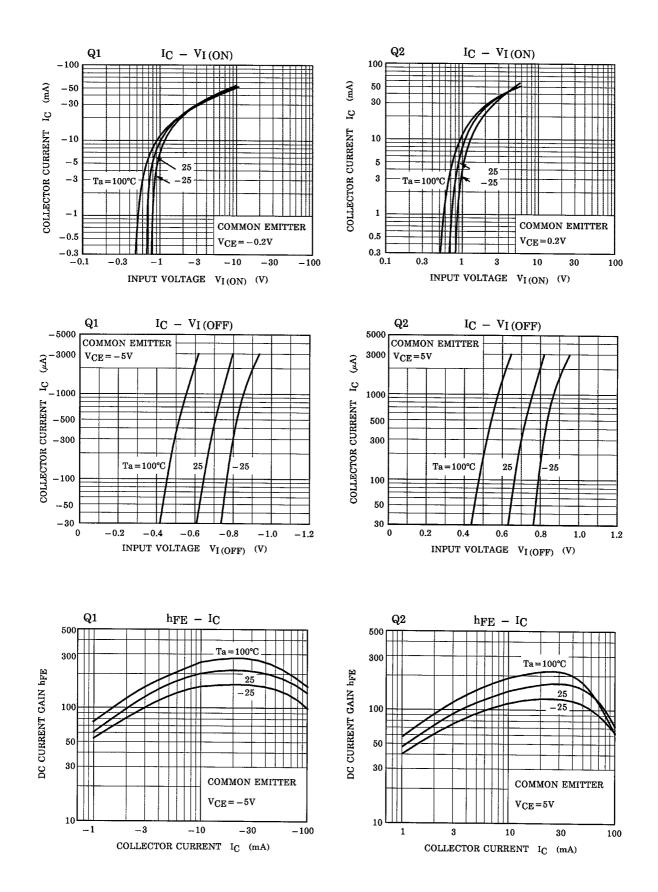
## Q2 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current	I <sub>CBO</sub>	_	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0	_	_	100	nA	
	ICEO		V <sub>CE</sub> = 50V, I <sub>B</sub> = 0	-	-	500		
Emitter cut-off current	I <sub>EBO</sub>		V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	0.074		0.138	mA	
DC current gain	h <sub>FE</sub>	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA	80	_	_	_	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	_	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0.25mA	_	0.1	0.3	V	
Input voltage (ON)	V <sub>I (ON)</sub>	_	V <sub>CE</sub> = 0.2V, I <sub>C</sub> = 5mA	0.7	_	1.3	V	
Input voltage (OFF)	V <sub>I (OFF)</sub>	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.1mA	0.5	_	0.8	V	
Transition frequency	f <sub>T</sub>	_	V <sub>CE</sub> = 10V, I <sub>C</sub> = 5mA	_	250	_	MHz	
Collector output capacitance	C <sub>ob</sub>	_	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1 MHz	_	3	6	pF	

## Q1, Q2 Common Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input resistor	R1		—	3.29	4.7	6.11	kΩ
Resistor ratio	R1/R2	—	—	0.09	0.1	0.11	—

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